



Attorney's Docket No.: 42P16680

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:)

Justin K. Brask et al.)

Application No.: 10/750,061)

Filed: December 30, 2003)

For: NONPLANAR TRANSISTORS WITH)
METAL GATE ELECTRODES)

Examiner: Lindsay Jr., Walter Lee

Art Unit: 2812

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

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Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: February 15, 2006,


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(use as many sheets as necessary)

Sheet 1 of 2

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| Application Number | 10/750,061 |
| Filing Date | December 30, 2003 |
| First Named Inventor: | Justin K. Brask, et al. |
| Art Unit | 2812 |
| Examiner Name | Lindsay, Jr., Walter L. |
| Attorney Docket No.: | 42P16680 |

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| | | | | Examiner Name | Lindsay Jr., Walter Lee |
| Sheet | 2 | of | 2 | Attorney Docket Number | 42P16680 |
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